



DMT6005LPS

60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

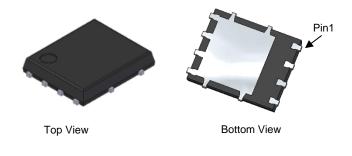
BV _{DSS}	Rds(on) Max	I _D T _C = +25°C
60V	$4.5 \text{m}\Omega$ @ $V_{GS} = 10V$	125A
607	$6.5 \text{m}\Omega$ @ V _{GS} = 4.5V	108A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- High Frequency Switching
- Synchronized Rectification
- DC-DC Converters

Site1:



PowerDI5060-8

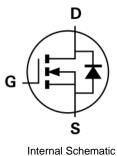
Features

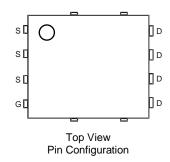
- 100% Unclamped Inductive Switching (UIS) Test in Production —
 Ensures More Reliable and Robust End Application
- Low RDS(ON) Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

Mechanical Data

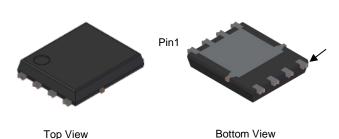
- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

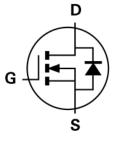




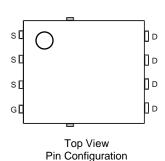
Site2:

PowerDI5060-8 (SWP) (Type UX)





Internal Schematic



Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

PowerDI is a registered trademark of Diodes Incorporated.



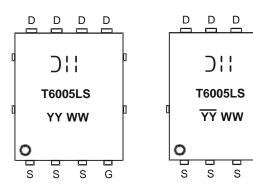
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6005LPS-13	PowerDI5060-8	2,500/Tape & Reel
DMT6005LPS-13	PowerDI5060-8 (SWP) (Type UX)	2,500/Tape & Reel

Note:

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Maximum Ratings $(@T_A = +25^{\circ}C, unless otherwise specified.)$

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	ΙD	18.4 14.7	А
Continuous Drain Current (Note 6) $ T_C = +25^{\circ}C $ $ T_C = +70^{\circ}C $		ID	125 100	А
Maximum Continuous Body Diode Forward Current (Note 6)		Is	125	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	500	Α
Avalanche Current, L = 1mH		las	14.8	Α
Avalanche Energy, L = 1mH		E _{AS}	98	mJ

G

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	47	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P_{D}	125	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).



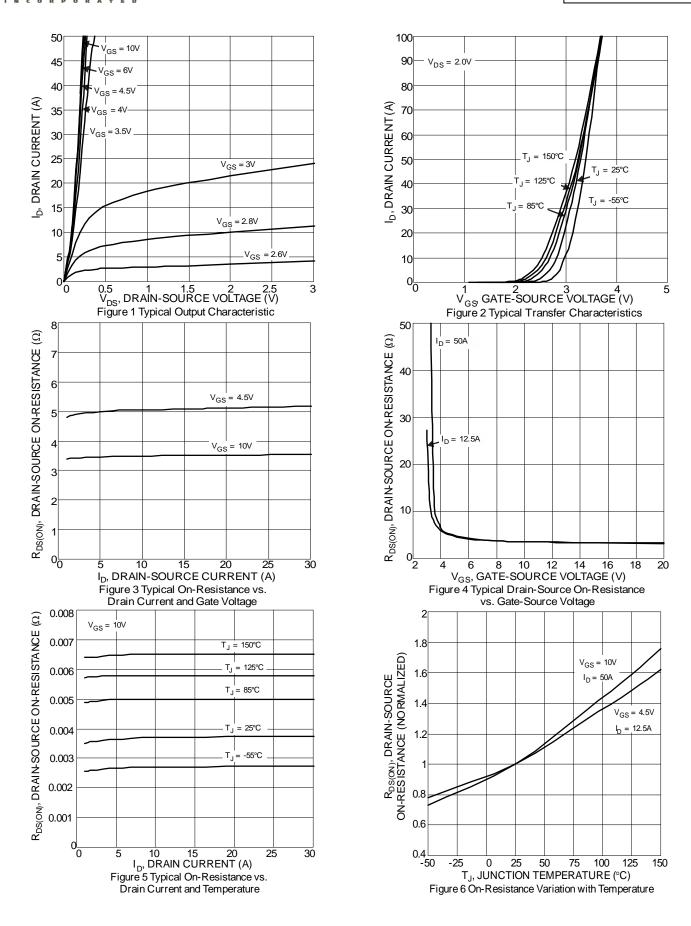
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_		V	$V_{GS} = 0V$, $I_D = 1mA$
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(th)	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	Descen	_	3.5	4.5	mΩ	$V_{GS} = 10V, I_{D} = 50A$
Static Dialif-Source Off-Resistance	RDS(ON)	_	5	6.5	11122	$V_{GS} = 4.5V, I_{D} = 12.5A$
Diode Forward Voltage	V _{SD}	_	0.9	_	V	$V_{GS} = 0V, I_{S} = 50A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	2,962	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	Coss	_	965.2		pF	
Reverse Transfer Capacitance	Crss	_	59.8			
Gate Resistance	Rg	_	0.66	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (Vgs = 10V)	Qg	_	47.1	_		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	23.1	_	nC	V _{DD} = 30V, I _D = 50A
Gate-Source Charge	Qgs	_	10.2	_	nc nc	
Gate-Drain Charge	Qgd	_	12.5	_		
Turn-On Delay Time	t _{D(ON)}	_	8.3	_		
Turn-On Rise Time	t _R	_	9.4	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 30A, R_{G} = 3.3\Omega$
Turn-Off Delay Time	tD(OFF)	_	22	_	ns	
Turn-Off Fall Time	tF	_	8.9	_		
Body Diode Reverse Recovery Time	trr	_	40.4	_	ns	I_ 200 di/dt 4000/
Body Diode Reverse Recovery Charge	Qrr	_	49.7	_	nC	-I _F = 30A, di/dt = 100A/μs

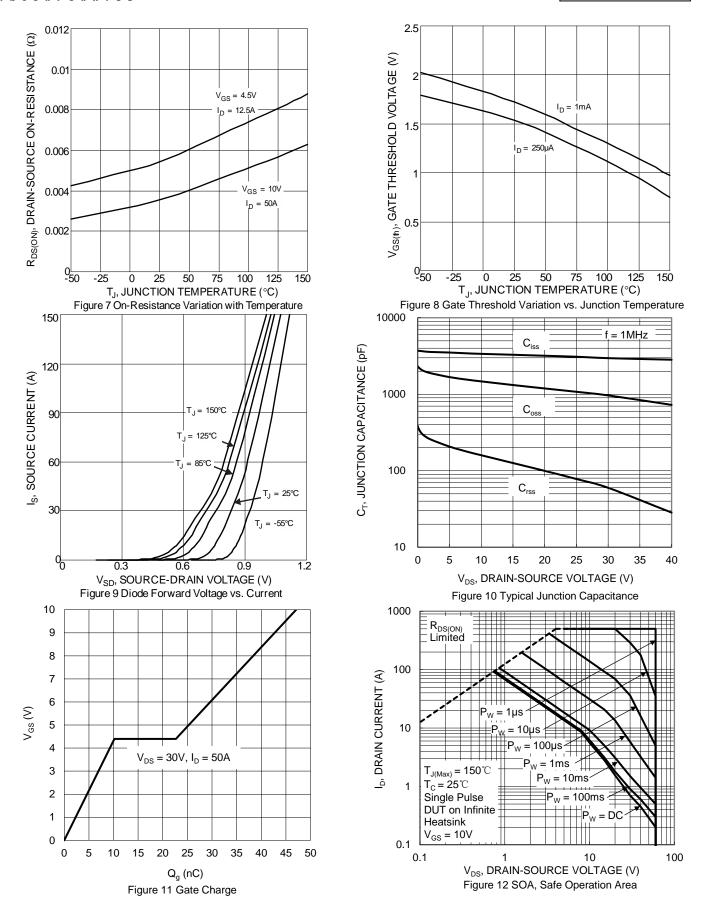
Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.











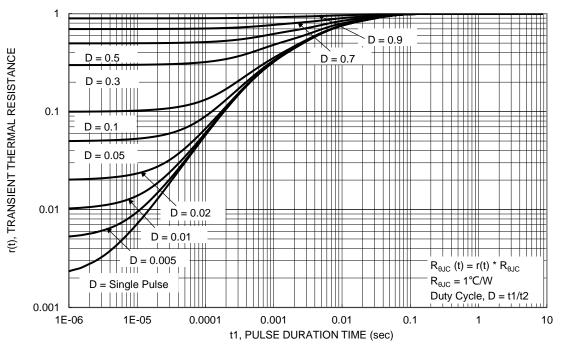


Figure 13 Transient Thermal Resistance

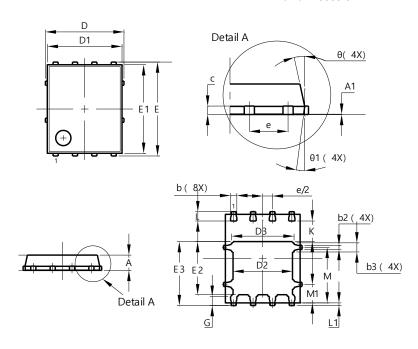


Package Outline Dimensions

 $\label{please} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

Site1:

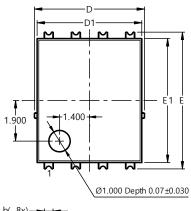
PowerDI5060-8

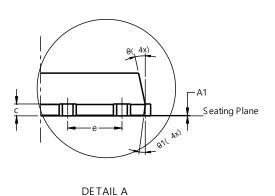


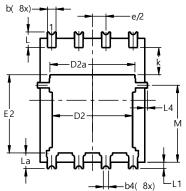
PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D		5.15 BSC	;	
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	(6.15 BSC	;	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	•	1.27 BSC	;	
G	0.51	0.71	0.61	
K	0.51	-	_	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
M	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

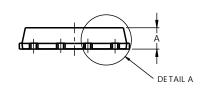
Site2:

PowerDI5060-8 (SWP) (Type UX)







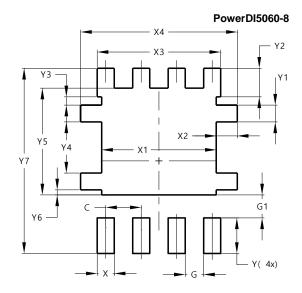


PowerDI5060-8 (SWP) (Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4	C).25REF		
С	0.230	0.330	0.277	
D	5	.15 BS0	\sim	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
Е	6	.40 BS0		
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е		.27BSC	;	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				



Suggested Pad Layout

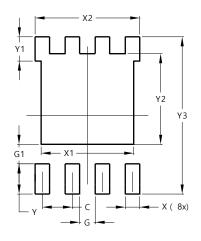
Please see http://www.diodes.com/package-outlines.html for the latest version. **Site1:**



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site2:

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value	
Dimensions	(in mm)	
С	1.270	
G	0.660	
G1	0.820	
Х	0.610	
X1	4.100	
X2	4.420	
Y	1.270	
Y1	1.020	
Y2	3.810	
Y3	6.610	



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